

AMENDMENTS

In the Claims:

Please add new claim 16.

Please amend claims 1, 4 and 13-15 as follows:

- SAC*
- B1*
1. (Amended) A gallium nitride compound semiconductor light-emitting diode comprising:
a substrate;
an n-type electrode region comprising an n-type transmissive electrode;
a gallium nitride compound semiconductor multilayer structure including an active layer; and
a p-type electrode region comprising a p-type transmissive electrode, wherein the n-type transmissive electrode and p-type transmissive electrode are thin films so as to be substantially transparent.

- B2*
4. (Amended) A gallium nitride compound semiconductor light-emitting diode according to claim 1, wherein the n-type transmissive electrode is formed around a circumference of the p-type transmissive electrode.

- B3*
- B3*
13. (Amended) A gallium nitride compound semiconductor light-emitting diode comprising:
a substrate;
an n-type electrode region comprising an n-type transmissive electrode;
a gallium nitride compound semiconductor multilayer structure including an active layer;
and
a p-type electrode region comprising a p-type transmissive electrode, wherein the n-type transmissive electrode is formed on a side face of the substrate, a side face of the buffer layer, and a side face of the n-type gallium nitride compound semiconductor layer in a region neighboring the buffer layer.

B3

14. (Amended) A gallium nitride compound semiconductor light emitting diode comprising:

a substrate;

an n-type electrode region comprising an n-type transmissive electrode;

a buffer layer provided on the substrate;

a gallium nitride compound semiconductor multilayer

structure including an active layer provided on the buffer layer; and

a p-type electrode region comprising a p-type transmissive electrode provided on the gallium nitride compound semiconductor multilayer structure, wherein

the n-type transmissive electrode is formed on the lower face of the substrate, a side face of the substrate, a side face of the buffer layer, and a side face of the n-type gallium nitride compound semiconductor multilayer structure in a region neighboring the buffer layer, and

wherein the n-type transmissive electrode comprises an oxide semiconductor.

B3

15. (Amended) A gallium nitride compound semiconductor light-emitting diode comprising:

a substrate;

an n-type electrode region comprising an n-type transmissive electrode;

a gallium nitride compound semiconductor multilayer structure including an active layer; and

a p-type electrode region comprising a p-type transmissive electrode, wherein

the n-type transmissive electrode and p-type transmissive electrode are films so as to be substantially transparent, and

wherein the n-type transmissive electrode comprises a thick film of ITO.

B4

16. (New) A gallium nitride compound semiconductor light-emitting diode according to claim 4, wherein the n-type transmissive electrode is formed completely around the circumference of the p-type transmissive electrode.